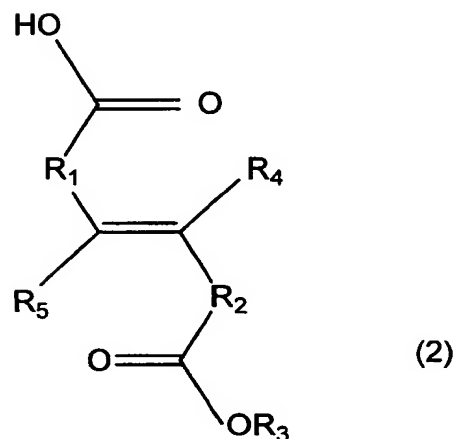
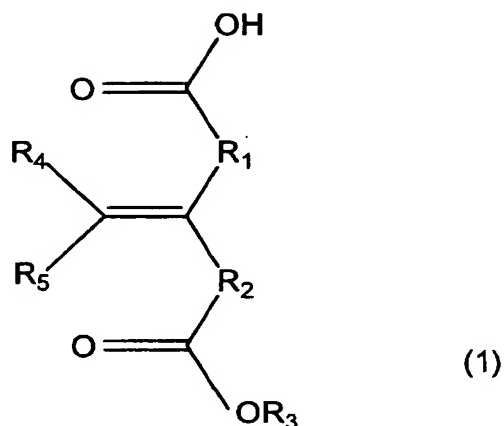


ABSTRACT

A negative resist composition includes a polymer having any one of dicarboxylate monoester compounds represented by the following general formulae (1) and (2) as a monomer component:



wherein, R_1 and R_2 represent alkyl chains having 0 to 5 carbon atoms, R_3 represents a substituent having at least two or more alicyclic structures, and R_4 and R_5 represent hydrogen atoms or alkyl groups having 1 to 8 carbon atoms. A method for forming a resist pattern uses the above negative resist composition. By containing the polymer, a resistance to dry etching and a resistance to electron beam from a scanning electron microscope (SEM) are enhanced as well as a solubility in an alkali developing solution is maintained.